



DMP2012SN

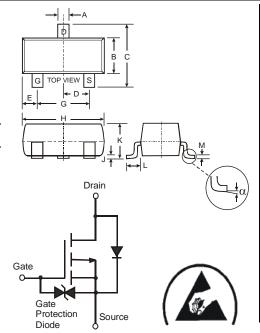
P-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

Features

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Lead Free By Design/RoHS Compliant (Note 2)
- **ESD Protected Gate**
- "Green" Device (Note 4)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SC-59
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture sensitivity: Level 1 per J-STD-020C
- Terminals: Finish Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Marking: See Last Page
- Ordering & Date Code Information: See Last Page
- Weight: 0.008 grams (approximate)



SC-59								
Dim	Min	Max						
Α	0.30	0.50						
В	1.40	1.80						
С	2.50	3.00						
D	0.85	1.05						
Е	0.30	0.70						
G	1.70	2.10						
Н	2.70	3.10						
J	_	0.10						
K	1.00	1.40						
L	0.55	0.70						
М	0.10	0.35						
α	0°	8°						
All Dimensions in mm								

EQUIVALENT CIRCUIT

ESD protected

Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V _{DSS}	-20	V	
Gate-Source Voltage	V _{GSS}	±12	V	
Drain Current (Note 1) Steady State	I _D	-0.7	А	
Pulsed Drain Current (Note 3)	I _{DM}	-2.8	A	
Total Power Dissipation (Note 1)	P _d	500	mW	
Thermal Resistance, Junction to Ambient	$R_{ heta JA}$	250	°C/W	
Operating and Storage Temperature Range	T _i , T _{STG}	-65 to +150	°C	

Notes:

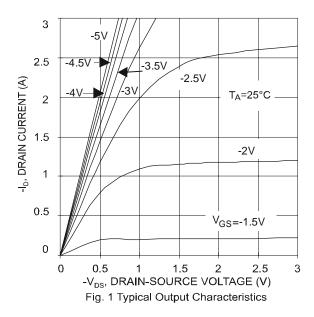
- Device mounted on FR-4 PCB. 1.
- 2. No purposefully added lead.
- Pulse width ≤10μS, Duty Cycle ≤1%.
- Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.

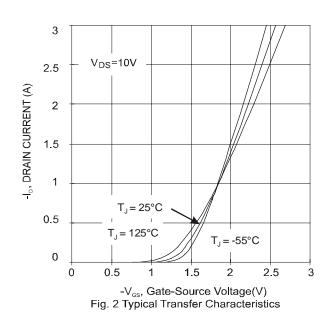


Electrical Characteristics $@T_A = 25^{\circ}C$ unless otherwise specified

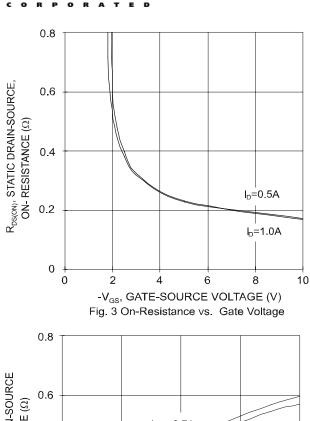
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition			
OFF CHARACTERISTICS (Note 5)									
Drain-Source Breakdown Voltage	BV _{DSS}	-20	_		V	$V_{GS} = 0V, I_D = 250mA$			
Zero Gate Voltage Drain Current	I _{DSS}	_	_	-10	μА	V _{DS} = -20V, V _{GS} = 0V			
Gate-Body Leakage	I _{GSS}	_	_	±10	μА	$V_{GS} = \pm 12V, V_{DS} = 0V$			
ON CHARACTERISTICS (Note 5)			•	•	•				
Gate Threshold Voltage	V _{GS(th)}	-0.5	_	-1.2	V	$V_{DS} = V_{GS}, I_D = -250 \mu A$			
Static Drain-Source On-Resistance	R _{DS (ON)}	_	0.23 0.37	0.30 0.50	Ω	$V_{GS} = -4.5V$, $I_{D} = -0.4A$ $V_{GS} = -2.5V$, $I_{D} = -0.4A$			
Forward Transfer Admittance	Y _{fs}	_	1.5		S	$V_{DS} = -10V, I_D = 0.4A$			
Diode Forward Voltage (Note 5)	V _{SD}	_	-0.8	-1.1	V	$V_{GS} = 0V, I_{S} = -0.7A$			
DYNAMIC CHARACTERISTICS			•	•	•	•			
Input Capacitance	C _{iss}	_	180		pF				
Output Capacitance	C _{oss}	_	120	_	pF	$V_{DS} = -10V, V_{GS} = 0V$ f = 1.0MHz			
Reverse Transfer Capacitance	C _{rss}	_	50		pF	1 - 1.000112			
SWITCHING CHARACTERISTICS			_						
Turn-On Delay Time	t _{D(ON)}	_	5		ns				
Turn-Off Delay Time	t _{D(OFF)}	_	55		ns	$V_{DD} = -10V, I_{D} = -0.4A,$			
Turn-On Rise Time	t _r		20		ns	$V_{GS} = -5.0V$, $R_{GEN} = 50\Omega$			
Turn-Off Fall Time	t _f		70	_	ns				

5. Short duration test pulse used to minimize self-heating effect. Notes:









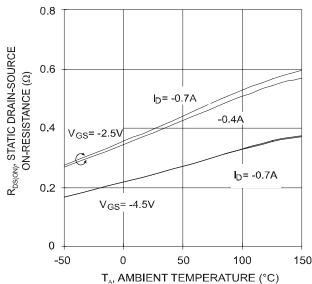
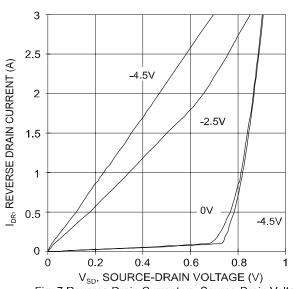
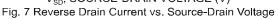


Fig. 5 On-Resistance Variation with Temperature





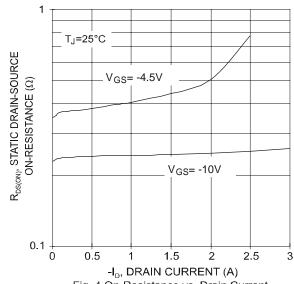


Fig. 4 On-Resistance vs. Drain Current

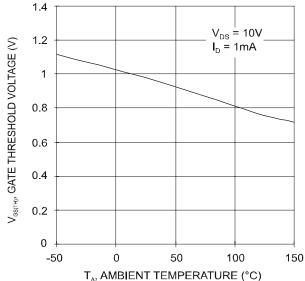


Fig. 6 Gate Threshold Voltage vs. Temperature

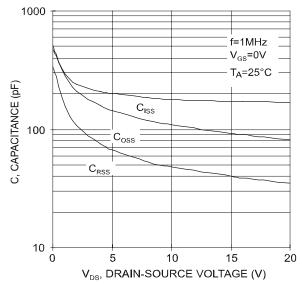


Fig. 8: Typical Junction Capacitance

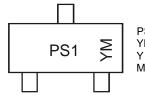


Ordering Information (Note 6)

Device	Packaging	Shipping
DMP2012SN-7	SC-59	3000/Tape & Reel

Notes: 6. For Packaging Details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information



PS1 = Product Type Marking Code YM = Date Code Marking

Y = Year ex: T = 2006 M = Month ex: 9 = September

Date Code Key

Year	2006		2007		2008	2009		2010		2011	2012	
Code	Т		U		V W		X		Υ		Z	
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

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